

**Silicon PNP Power Transistors**

**2SA1063**

**DESCRIPTION**

- With TO-3 package
- Low collector saturation voltage
- High transition frequency

**APPLICATIONS**

- Designed for general purpose switching and amplifier applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

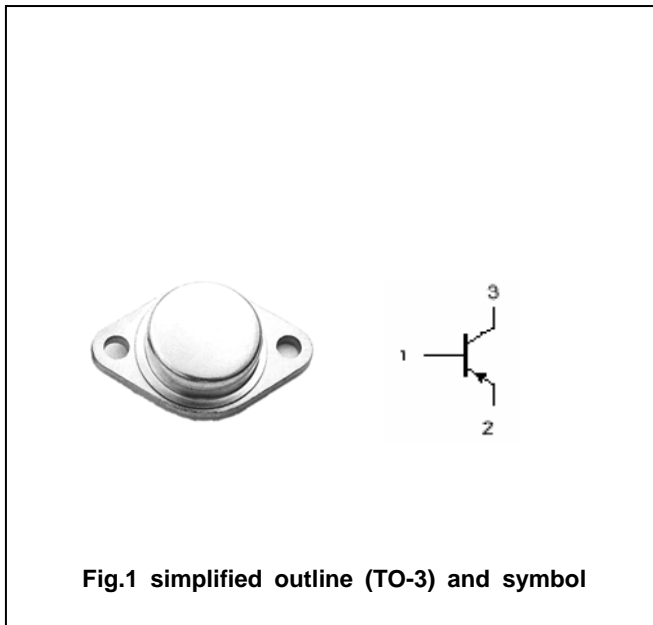


Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-6	A
I <sub>CM</sub>	Collector current-peak		-10	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	80	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## 2SA1063

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA ; I <sub>B</sub> =0	-150			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-0.4A			-2.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-5V			-1.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-150V ; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V ; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	40		280	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-5V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V		50		MHz

◆ h<sub>FE-1</sub> Classifications

R	Q	P	O
40-80	60-120	90-180	140-280

PACKAGE OUTLINE

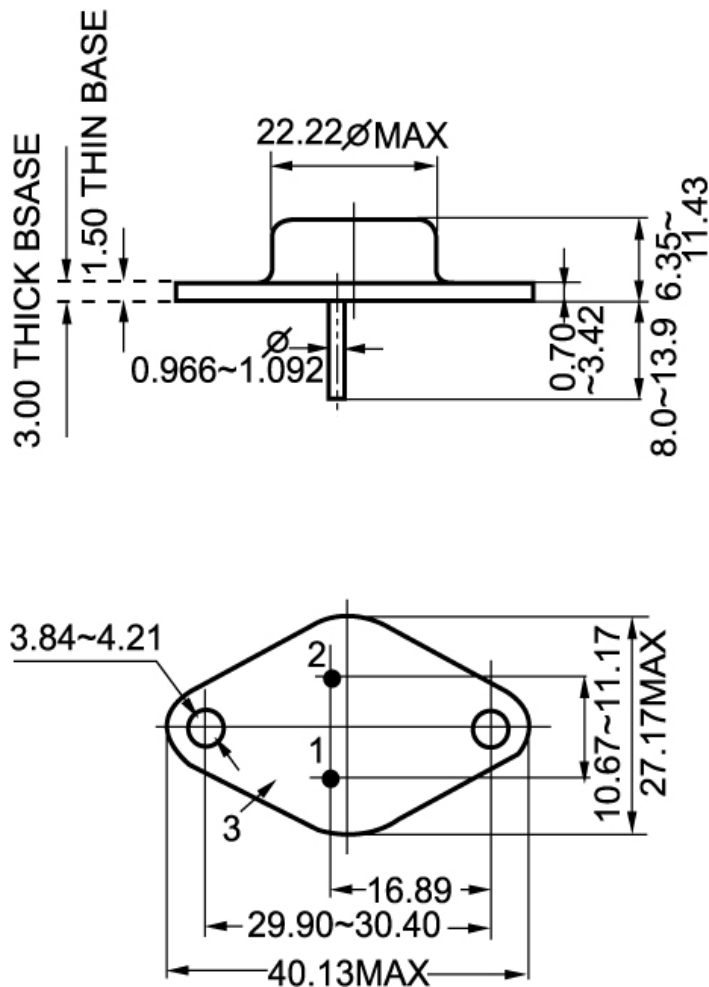


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.1$ mm)